

Abstracts

A Monolithic High Power Ka Band PIN Switch

J.V. Bellantoni, D.C. Bartle, D. Payne, G. McDermott, S. Bandla, R. Tayrani and L. Raffaelli. "A Monolithic High Power Ka Band PIN Switch." 1989 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 89.1 (1989 [MCS]): 47-50.

A high power Ka Band SPDT switch using monolithic GaAs epitaxial PIN diode technology is presented. Insertion loss is 0.7 dB at 35 GHz, and isolation is better than 32 dB from 30 to 40 GHz. The power handling capability is at least +38 dBm pulsed and +35 dBm CW. Switching speed rise and fall times are 2 ns.

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